

NXB0102

Dual supply translating transceiver; auto direction sensing;
3-state

Rev. 01 — 8 June 2010

Product data sheet

1. General description

The NXB0102 is a 2-bit, dual supply translating transceiver with auto direction sensing, that enables bidirectional voltage level translation. It features two data input-output ports (An and Bn), one output enable input (OE) and two supply pins ($V_{CC(A)}$ and $V_{CC(B)}$). $V_{CC(A)}$ can be supplied at any voltage between 1.2 V and 3.6 V and $V_{CC(B)}$ can be supplied at any voltage between 1.65 V and 5.5 V, making the device suitable for translating between any of the low voltage nodes (1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.3 V and 5.0 V).

Pins An and OE are referenced to $V_{CC(A)}$ and pins Bn are referenced to $V_{CC(B)}$. A LOW level at pin OE causes the outputs to assume a high-impedance OFF-state. This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range:
 - ◆ $V_{CC(A)}$: 1.2 V to 3.6 V and $V_{CC(B)}$: 1.65 V to 5.5 V
- I_{OFF} circuitry provides partial Power-down mode operation
- Inputs accept voltages up to 5.5 V
- ESD protection:
 - ◆ HBM JESD22-A114E Class 2 exceeds 2500 V for A port
 - ◆ HBM JESD22-A114E Class 3B exceeds 15000 V for B port
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101E exceeds 1500 V
- Latch-up performance exceeds 100 mA per JESD 78B Class II
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$



3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
NXB0102DP	−40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
NXB0102GT	−40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1
NXB0102GD	−40 °C to +125 °C	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body 3 × 2 × 0.5 mm	SOT996-2
NXB0102GF	−40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1 × 0.5 mm	SOT1089

4. Marking

Table 2. Marking

Type number	Marking code ^[1]
NXB0102DP	t02
NXB0102GT	t02
NXB0102GD	t02
NXB0102GF	t2

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

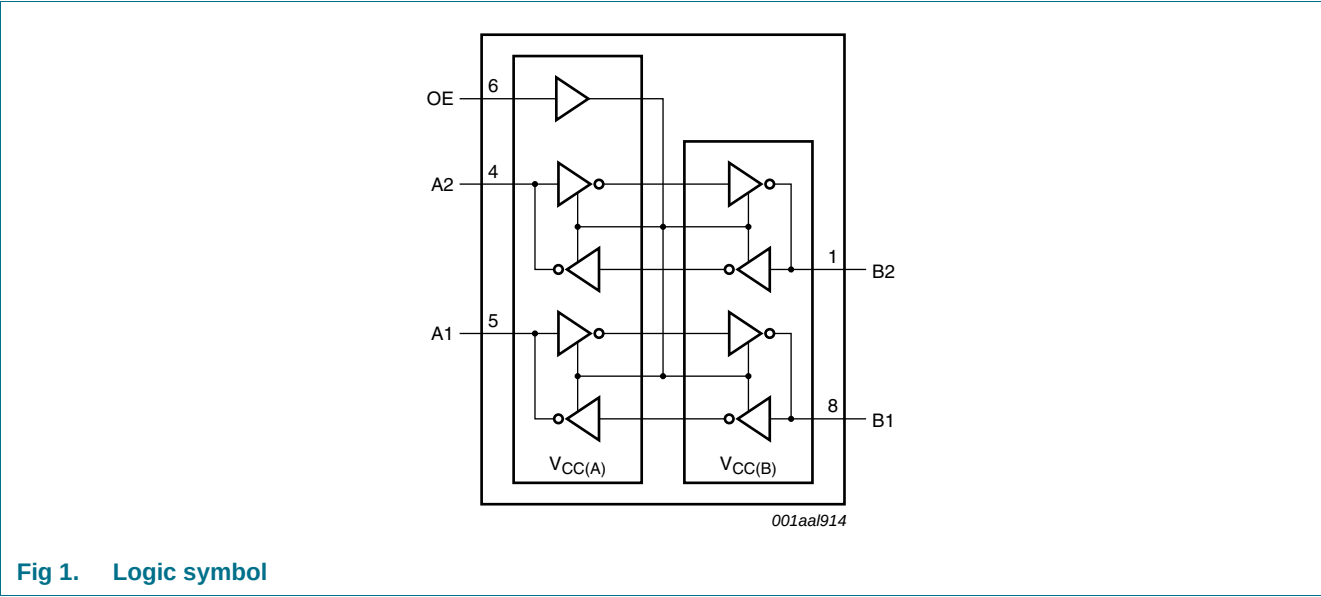
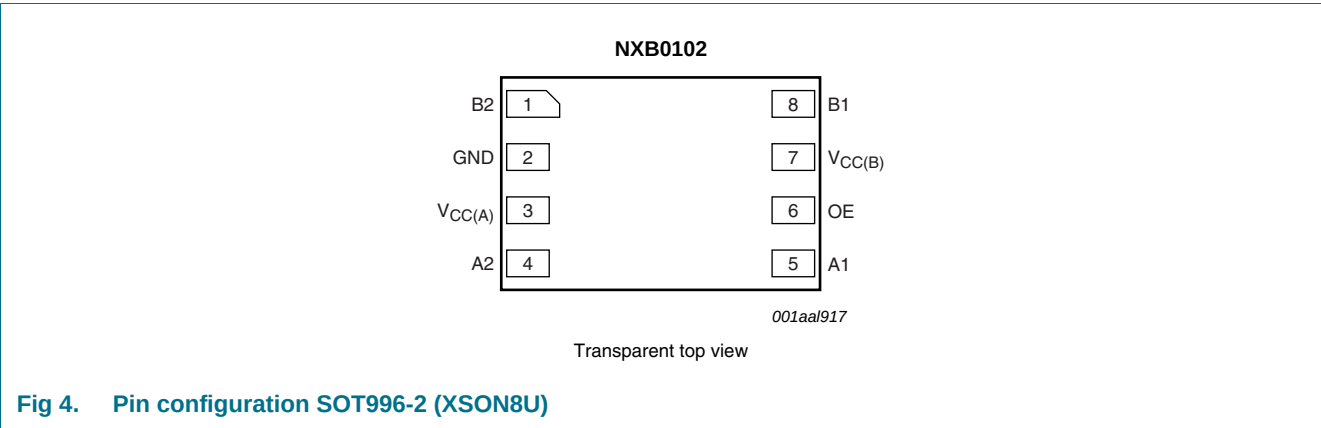
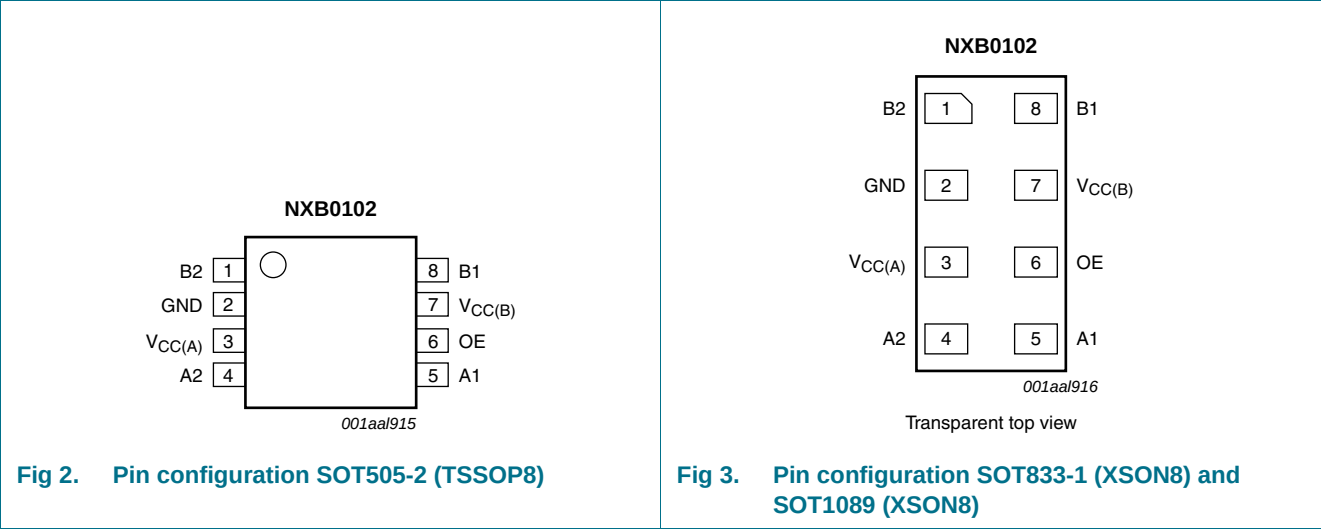


Fig 1. Logic symbol

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description		
Symbol	Pin	Description
B2, B1	1, 8	data input or output (referenced to V _{CC(B)})
GND	2	ground (0 V)
V _{CC(A)}	3	supply voltage A
A2, A1	4, 5	data input or output (referenced to V _{CC(A)})
OE	6	output enable input (active HIGH; referenced to V _{CC(A)})
V _{CC(B)}	7	supply voltage B

7. Functional description

Table 4. Function table^[1]

Supply voltage		Input	Input/output	
V _{CC(A)}	V _{CC(B)}	OE	An	Bn
1.2 V to V _{CC(B)}	1.65 V to 5.5 V	L	Z	Z
1.2 V to V _{CC(B)}	1.65 V to 5.5 V	H	input or output	output or input
GND ^[2]	GND ^[2]	X	Z	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

[2] When either V_{CC(A)} or V_{CC(B)} is at GND level, the device goes into Power-down mode.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC(A)}	supply voltage A		-0.5	+6.5	V
V _{CC(B)}	supply voltage B		-0.5	+6.5	V
V _I	input voltage		^[1] -0.5	+6.5	V
V _O	output voltage	Active mode	^{[1][2][3]} -0.5	V _{CCO} + 0.5	V
		Power-down or 3-state mode	^[1] -0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
I _O	output current	V _O = 0 V to V _{CCO}	^[2] -	±50	mA
I _{CC}	supply current	I _{CC(A)} or I _{CC(B)}	-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	^[4] -	250	mW

[1] The minimum input and minimum output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] V_{CCO} is the supply voltage associated with the output.

[3] V_{CCO} + 0.5 V should not exceed 6.5 V.

[4] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.
For XSON8 and XSON8U packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions^{[1][2]}

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		1.2	3.6	V
$V_{CC(B)}$	supply voltage B		1.65	5.5	V
V_I	input voltage		0	5.5	V
V_O	output voltage	Power-down or 3-state mode; $V_{CC(A)} = 1.2\text{ V to }3.6\text{ V};$ $V_{CC(B)} = 1.65\text{ V to }5.5\text{ V}$			
		A port	0	3.6	V
		B port	0	5.5	V
T_{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC(A)} = 1.2\text{ V to }3.6\text{ V};$ $V_{CC(B)} = 1.65\text{ V to }5.5\text{ V}$	-	40	ns/V

[1] The A and B sides of an unused I/O pair must be held in the same state, both at V_{CCI} or both at GND.

[2] $V_{CC(A)}$ must be less than or equal to $V_{CC(B)}$.

10. Static characteristics

Table 7. Typical static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); $T_{amb} = 25\text{ °C}$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{OH}	HIGH-level output voltage	A port; $V_{CC(A)} = 1.2\text{ V}; I_O = -20\text{ }\mu\text{A}$	-	1.1	-	V
V_{OL}	LOW-level output voltage	A port; $V_{CC(A)} = 1.2\text{ V}; I_O = 20\text{ }\mu\text{A}$	-	0.09	-	V
I_I	input leakage current	OE input; $V_I = 0\text{ V to }3.6\text{ V}; V_{CC(A)} = 1.2\text{ V to }3.6\text{ V};$ $V_{CC(B)} = 1.65\text{ V to }5.5\text{ V}$	-	-	± 1	μA
I_{OZ}	OFF-state output current	A or B port; $V_O = 0\text{ V to }V_{CCO}; V_{CC(A)} = 1.2\text{ V to }3.6\text{ V};$ $V_{CC(B)} = 1.65\text{ V to }5.5\text{ V}$	[1]	-	± 1	μA
I_{OFF}	power-off leakage current	A port; V_I or $V_O = 0\text{ V to }3.6\text{ V};$ $V_{CC(A)} = 0\text{ V}; V_{CC(B)} = 0\text{ V to }5.5\text{ V}$	-	-	± 1	μA
		B port; V_I or $V_O = 0\text{ V to }5.5\text{ V};$ $V_{CC(B)} = 0\text{ V}; V_{CC(A)} = 0\text{ V to }3.6\text{ V}$	-	-	± 1	μA
I_{CC}	supply current	$V_I = 0\text{ V or }V_{CCI}; I_O = 0\text{ A}$	[2]			
		$I_{CC(A)}; V_{CC(A)} = 1.2\text{ V}; V_{CC(B)} = 1.65\text{ V to }5.5\text{ V}$	-	0.05	-	μA
		$I_{CC(B)}; V_{CC(A)} = 1.2\text{ V}; V_{CC(B)} = 1.65\text{ V to }5.5\text{ V}$	-	3.3	-	μA
		$I_{CC(A)} + I_{CC(B)}; V_{CC(A)} = 1.2\text{ V}; V_{CC(B)} = 1.65\text{ V to }5.5\text{ V}$	-	3.5	-	μA
C_I	input capacitance	OE input; $V_{CC(A)} = 1.2\text{ V to }3.6\text{ V}; V_{CC(B)} = 1.65\text{ V to }5.5\text{ V}$	-	1.0	-	pF
$C_{I/O}$	input/output capacitance	A port; $V_{CC(A)} = 1.2\text{ V to }3.6\text{ V}; V_{CC(B)} = 1.65\text{ V to }5.5\text{ V}$	-	4.0	-	pF
		B port; $V_{CC(A)} = 1.2\text{ V to }3.6\text{ V}; V_{CC(B)} = 1.65\text{ V to }5.5\text{ V}$	-	7.5	-	pF

[1] V_{CCO} is the supply voltage associated with the output.

[2] V_{CCI} is the supply voltage associated with the input.

Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Max	Min	Max	
V_{IH}	HIGH-level input voltage	A or B port and OE input [1] $V_{CC(A)} = 1.2 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$	$0.65V_{CCI}$	-	$0.65V_{CCI}$	-	V
V_{IL}	LOW-level input voltage	A or B port and OE input [1] $V_{CC(A)} = 1.2 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$	-	$0.35V_{CCI}$	-	$0.35V_{CCI}$	V
V_{OH}	HIGH-level output voltage	$I_O = -20 \mu\text{A}$ [2] A port; $V_{CC(A)} = 1.4 \text{ V to } 3.6 \text{ V}$ B port; $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$	$V_{CCO} - 0.4$	-	$V_{CCO} - 0.4$	-	V
V_{OL}	LOW-level output voltage	$I_O = 20 \mu\text{A}$ [2] A port; $V_{CC(A)} = 1.4 \text{ V to } 3.6 \text{ V}$ B port; $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$	-	0.4	-	0.4	V
I_I	input leakage current	OE input; $V_I = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC(A)} = 1.2 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$	-	± 2	-	± 5	μA
I_{OZ}	OFF-state output current	A or B port; $V_O = 0 \text{ V or } V_{CCO};$ [2] $V_{CC(A)} = 1.2 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$	-	± 2	-	± 10	μA
I_{OFF}	power-off leakage current	A port; $V_I \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 0 \text{ V to } 5.5 \text{ V}$ B port; $V_I \text{ or } V_O = 0 \text{ V to } 5.5 \text{ V};$ $V_{CC(B)} = 0 \text{ V}; V_{CC(A)} = 0 \text{ V to } 3.6 \text{ V}$	-	± 2	-	± 10	μA

Table 8. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Max	Min	Max	
I_{CC}	supply current	$V_I = 0\text{ V}$ or V_{CCI} ; $I_O = 0\text{ A}$ [1]					
		$I_{CC(A)}$					
		OE = LOW; $V_{CC(A)} = 1.4\text{ V}$ to 3.6 V ; $V_{CC(B)} = 1.65\text{ V}$ to 5.5 V	-	3	-	15	μA
		OE = HIGH; $V_{CC(A)} = 1.4\text{ V}$ to 3.6 V ; $V_{CC(B)} = 1.65\text{ V}$ to 5.5 V	-	3	-	20	μA
		$V_{CC(A)} = 3.6\text{ V}$; $V_{CC(B)} = 0\text{ V}$	-	2	-	15	μA
		$V_{CC(A)} = 0\text{ V}$; $V_{CC(B)} = 5.5\text{ V}$	-	-2	-	-15	μA
		$I_{CC(B)}$					
		OE = LOW; $V_{CC(A)} = 1.4\text{ V}$ to 3.6 V ; $V_{CC(B)} = 1.65\text{ V}$ to 5.5 V	-	5	-	15	μA
		OE = HIGH; $V_{CC(A)} = 1.4\text{ V}$ to 3.6 V ; $V_{CC(B)} = 1.65\text{ V}$ to 5.5 V	-	5	-	20	μA
		$V_{CC(A)} = 3.6\text{ V}$; $V_{CC(B)} = 0\text{ V}$	-	-2	-	-15	μA
		$V_{CC(A)} = 0\text{ V}$; $V_{CC(B)} = 5.5\text{ V}$	-	2	-	15	μA
		$I_{CC(A)} + I_{CC(B)}$					
		$V_{CC(A)} = 1.4\text{ V}$ to 3.6 V ; $V_{CC(B)} = 1.65\text{ V}$ to 5.5 V	-	8	-	40	μA

[1] V_{CCI} is the supply voltage associated with the input.[2] V_{CCO} is the supply voltage associated with the output.

11. Dynamic characteristics

Table 9. Typical dynamic characteristics for temperature 25 °C [\[1\]](#)Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#); for waveforms see [Figure 5](#) and [Figure 6](#).

Symbol	Parameter	Conditions	V _{CC(B)}				Unit
			1.8 V	2.5 V	3.3 V	5.0 V	
V _{CC(A)} = 1.2 V; T _{amb} = 25 °C							
t _{pd}	propagation delay	A to B	5.9	4.8	4.4	4.2	ns
		B to A	5.6	4.8	4.5	4.4	ns
t _{en}	enable time	OE to A, B	0.5	0.5	0.5	0.5	μs
t _{dis}	disable time	OE to A; no external load [2]	6.9	6.9	6.9	6.9	ns
		OE to B; no external load [2]	9.5	8.6	8.5	8.0	ns
		OE to A	81	69	83	68	ns
		OE to B	81	69	83	68	ns
t _t	transition time	A port	4.0	4.0	4.1	4.1	ns
		B port	2.6	2.0	1.7	1.4	ns

Table 9. Typical dynamic characteristics for temperature 25 °C^[1] ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#); for waveforms see [Figure 5](#) and [Figure 6](#).

Symbol	Parameter	Conditions	V _{CC(B)}				Unit
			1.8 V	2.5 V	3.3 V	5.0 V	
t _{sk(o)}	output skew time	between channels ^[3]	0.2	0.2	0.2	0.2	ns
t _W	pulse width	data inputs	15	13	13	13	ns
f _{data}	data rate		70	80	80	80	Mbps

[1] t_{pd} is the same as t_{PLH} and t_{PHL}.

t_{en} is the same as t_{PZL} and t_{PZH}.

t_{dis} is the same as t_{PLZ} and t_{PHZ}.

t_t is the same as t_{THL} and t_{TLH}.

[2] Delay between OE going LOW and when the outputs are actually disabled.

[3] Skew between any two outputs of the same package switching in the same direction.

Table 10. Dynamic characteristics for temperature range –40 °C to +85 °C^[1]

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#); for wave forms see [Figure 5](#) and [Figure 6](#).

Symbol	Parameter	Conditions	V _{CC(B)}								Unit
			1.8 V ± 0.15 V		2.5 V ± 0.2 V		3.3 V ± 0.3 V		5.0 V ± 0.5 V		
			Min	Max	Min	Max	Min	Max	Min	Max	

V_{CC(A)} = 1.5 V ± 0.1 V

t _{pd}	propagation delay	A to B	1.4	12.9	1.2	10.1	1.1	10.0	0.8	9.9	ns
		B to A	0.9	14.2	0.7	12.0	0.4	11.7	0.3	13.7	ns
t _{en}	enable time	OE to A, B	-	1.0	-	1.0	-	1.0	-	1.0	µs
t _{dis}	disable time	OE to A; no external load ^[2]	1.0	11.9	1.0	11.9	1.0	11.9	1.0	11.9	ns
		OE to B; no external load ^[2]	1.0	16.9	1.0	15.2	1.0	14.1	1.0	13.8	ns
		OE to A	-	320	-	260	-	260	-	280	ns
		OE to B	-	-	200	-	200	-	200	-	ns
t _t	transition time	A port	0.9	5.1	0.9	5.1	0.9	5.1	0.9	5.1	ns
		B port	0.9	4.7	0.6	3.2	0.5	2.5	0.4	2.7	ns
t _{sk(o)}	output skew time	between channels ^[3]	-	0.5	-	0.5	-	0.5	-	0.5	ns
t _W	pulse width	data inputs	25	-	25	-	25	-	25	-	ns
f _{data}	data rate		-	40	-	40	-	40	-	40	Mbps

V_{CC(A)} = 1.8 V ± 0.15 V

t _{pd}	propagation delay	A to B	1.6	11.0	1.4	7.7	1.3	6.8	1.2	6.5	ns
		B to A	1.5	12.0	1.3	8.4	1.0	7.6	0.9	7.1	ns
t _{en}	enable time	OE to A, B	-	1.0	-	1.0	-	1.0	-	1.0	µs
t _{dis}	disable time	OE to A; no external load ^[2]	1.0	11.0	1.0	11.0	1.0	11.0	1.0	11.0	ns
		OE to B; no external load ^[2]	1.0	15.4	1.0	13.5	1.0	12.4	1.0	12.1	ns
		OE to A	-	260	-	230	-	230	-	230	ns
		OE to B	-	200	-	200	-	200	-	200	ns
t _t	transition time	A port	0.8	4.1	0.8	4.1	0.8	4.1	0.8	4.1	ns
		B port	0.9	4.7	0.6	3.2	0.5	2.5	0.4	2.7	ns

Table 10. Dynamic characteristics for temperature range -40°C to $+85^{\circ}\text{C}$ ^[1] ...continuedVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#); for wave forms see [Figure 5](#) and [Figure 6](#).

Symbol	Parameter	Conditions	V _{CC(B)}								Unit
			1.8 V ± 0.15 V		2.5 V ± 0.2 V		3.3 V ± 0.3 V		5.0 V ± 0.5 V		
			Min	Max	Min	Max	Min	Max	Min	Max	
t _{sk(o)}	output skew time	between channels [3]	-	0.5	-	0.5	-	0.5	-	0.5	ns
t _W	pulse width	data inputs	20	-	17	-	17	-	17	-	ns
f _{data}	data rate		-	49	-	60	-	60	-	60	Mbps
V _{CC(A)} = 2.5 V ± 0.2 V											
t _{pd}	propagation delay	A to B	-	-	1.1	6.3	1.0	5.2	0.9	4.7	ns
		B to A	-	-	1.2	6.6	1.1	5.1	0.9	4.4	ns
t _{en}	enable time	OE to A, B	-	-	-	1.0	-	1.0	-	1.0	μs
t _{dis}	disable time	OE to A; no external load [2]	-	-	1.0	9.2	1.0	9.2	1.0	9.2	ns
		OE to B; no external load [2]	-	-	1.0	11.9	1.0	10.7	1.0	10.2	ns
		OE to A	-	-	-	200	-	200	-	200	ns
		OE to B	-	-	-	200	-	200	-	200	ns
t _t	transition time	A port	-	-	0.7	3.0	0.7	3.0	0.7	3.0	ns
		B port	-	-	0.7	3.2	0.5	2.5	0.4	2.7	ns
t _{sk(o)}	output skew time	between channels [3]	-	-	-	0.5	-	0.5	-	0.5	ns
t _W	pulse width	data inputs	-	-	12	-	10	-	10	-	ns
f _{data}	data rate		-	-	-	85	-	100	-	100	Mbps
V _{CC(A)} = 3.3 V ± 0.3 V											
t _{pd}	propagation delay	A to B	-	-	-	-	0.9	4.7	0.8	4.0	ns
		B to A	-	-	-	-	1.0	4.9	0.9	3.8	ns
t _{en}	enable time	OE to A, B	-	-	-	-	-	1.0	-	1.0	μs
t _{dis}	disable time	OE to A; no external load [2]	-	-	-	-	1.0	9.2	1.0	9.2	ns
		OE to B; no external load [2]	-	-	-	-	1.0	10.1	1.0	9.6	ns
		OE to A	-	-	-	-	-	260	-	260	ns
		OE to B	-	-	-	-	-	200	-	200	ns
t _t	transition time	A port	-	-	-	-	0.7	2.5	0.7	2.5	ns
		B port	-	-	-	-	0.5	2.5	0.4	2.7	ns
t _{sk(o)}	output skew time	between channels [3]	-	-	-	-	-	0.5	-	0.5	ns
t _W	pulse width	data inputs	-	-	-	-	10	-	10	-	ns
f _{data}	data rate		-	-	-	-	-	100	-	100	Mbps

- [1] t_{pd} is the same as t_{PLH} and t_{PHL} .
 t_{en} is the same as t_{PZL} and t_{PZH} .
 t_{dis} is the same as t_{PLZ} and t_{PHZ} .
 t_t is the same as t_{THL} and t_{TLH} .

- [2] Delay between OE going LOW and when the outputs are actually disabled.

- [3] Skew between any two outputs of the same package switching in the same direction.

Table 11. Dynamic characteristics for temperature range –40 °C to +125 °C^[1]

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#); for wave forms see [Figure 5](#) and [Figure 6](#).

Symbol	Parameter	Conditions	V _{CC(B)}								Unit
			1.8 V ± 0.15 V		2.5 V ± 0.2 V		3.3 V ± 0.3 V		5.0 V ± 0.5 V		
			Min	Max	Min	Max	Min	Max	Min	Max	
V _{CC(A)} = 1.5 V ± 0.1 V											
t _{pd}	propagation delay	A to B	1.4	15.9	1.2	13.1	1.1	13.0	0.8	12.9	ns
		B to A	0.9	17.2	0.7	15.0	0.4	14.7	0.3	16.7	ns
t _{en}	enable time	OE to A, B	-	1.0	-	1.0	-	1.0	-	1.0	µs
t _{dis}	disable time	OE to A; no external load [2]	1.0	12.5	1.0	12.5	1.0	12.5	1.0	12.5	ns
		OE to B; no external load [2]	1.0	18.1	1.0	16.2	1.0	14.9	1.0	14.6	ns
		OE to A	-	340	-	280	-	280	-	300	ns
		OE to B	-	220	-	220	-	220	-	220	ns
t _t	transition time	A port	0.9	7.1	0.9	7.1	0.9	7.1	0.9	7.1	ns
		B port	0.9	6.5	0.6	5.2	0.5	4.8	0.4	4.7	ns
t _{sk(o)}	output skew time	between channels [3]	-	0.5	-	0.5	-	0.5	-	0.5	ns
t _W	pulse width	data inputs	25	-	25	-	25	-	25	-	ns
f _{data}	data rate		-	40	-	40	-	40	-	40	Mbps
V _{CC(A)} = 1.8 V ± 0.15 V											
t _{pd}	propagation delay	A to B	1.6	14.0	1.4	10.7	1.3	9.8	1.2	9.5	ns
		B to A	1.5	15.0	1.3	11.4	1.0	10.6	0.9	10.1	ns
t _{en}	enable time	OE to A, B	-	1.0	-	1.0	-	1.0	-	1.0	µs
t _{dis}	disable time	OE to A; no external load [2]	1.0	11.5	1.0	11.5	1.0	11.5	1.0	11.5	ns
		OE to B; no external load [2]	1.0	16.5	1.0	14.5	1.0	13.3	1.0	12.7	ns
		OE to A	-	280	-	250	-	250	-	250	ns
		OE to B	-	220	-	220	-	220	-	220	ns
t _t	transition time	A port	0.8	6.2	0.8	6.1	0.8	6.1	0.8	6.1	ns
		B port	0.9	5.8	0.6	5.2	0.5	4.8	0.4	4.7	ns
t _{sk(o)}	output skew time	between channels [3]	-	0.5	-	0.5	-	0.5	-	0.5	ns
t _W	pulse width	data inputs	22	-	19	-	19	-	19	-	ns
f _{data}	data rate		-	45	-	55	-	55	-	55	Mbps
V _{CC(A)} = 2.5 V ± 0.2 V											
t _{pd}	propagation delay	A to B	-	-	1.1	9.3	1.0	8.2	0.9	7.7	ns
		B to A	-	-	1.2	9.6	1.1	8.1	0.9	7.4	ns
t _{en}	enable time	OE to A, B	-	-	-	1.0	-	1.0	-	1.0	µs
t _{dis}	disable time	OE to A; no external load [2]	-	-	1.0	9.6	1.0	9.6	1.0	9.6	ns
		OE to B; no external load [2]	-	-	1.0	12.6	1.0	11.4	1.0	10.8	ns
		OE to A	-	-	-	220	-	220	-	220	ns
		OE to B	-	-	-	220	-	220	-	220	ns
t _t	transition time	A port	-	-	0.7	5.0	0.7	5.0	0.7	5.0	ns
		B port	-	-	0.7	4.6	0.5	4.8	0.4	4.7	ns

Table 11. Dynamic characteristics for temperature range -40°C to $+125^{\circ}\text{C}$ ^[1] ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#); for wave forms see [Figure 5](#) and [Figure 6](#).

Symbol	Parameter	Conditions	V _{CC(B)}								Unit
			1.8 V ± 0.15 V		2.5 V ± 0.2 V		3.3 V ± 0.3 V		5.0 V ± 0.5 V		
			Min	Max	Min	Max	Min	Max	Min	Max	
t _{sk(o)}	output skew time	between channels [3]	-	-	-	0.5	-	0.5	-	0.5	ns
t _W	pulse width	data inputs;	-	-	14	-	13	-	10	-	ns
f _{data}	data rate		-	-	-	75	-	80	-	100	Mbps
V _{CC(A)} = 3.3 V ± 0.3 V											
t _{pd}	propagation delay	A to B	-	-	-	-	0.9	7.7	0.8	7.0	ns
		B to A	-	-	-	-	1.0	7.9	0.9	6.8	ns
t _{en}	enable time	OE to A, B	-	-	-	-	-	1.0	-	1.0	μs
t _{dis}	disable time	OE to A; no external load [2]	-	-	-	-	1.0	9.5	1.0	9.5	ns
		OE to B; no external load [2]	-	-	-	-	1.0	10.7	1.0	9.6	ns
		OE to A	-	-	-	-	-	280	-	280	ns
		OE to B	-	-	-	-	-	220	-	220	ns
t _t	transition time	A port	-	-	-	-	0.7	4.5	0.7	4.5	ns
		B port	-	-	-	-	0.5	4.1	0.4	4.7	ns
t _{sk(o)}	output skew time	between channels [3]	-	-	-	-	-	0.5	-	0.5	ns
t _W	pulse width	data inputs	-	-	-	-	10	-	10	-	ns
f _{data}	data rate		-	-	-	-	-	100	-	100	Mbps

- [1] t_{pd} is the same as t_{PLH} and t_{PHL} .
 t_{en} is the same as t_{PZL} and t_{PZH} .
 t_{dis} is the same as t_{PLZ} and t_{PHZ} .
 t_t is the same as t_{THL} and t_{TLH} .

- [2] Delay between OE going LOW and when the outputs are actually disabled.

- [3] Skew between any two outputs of the same package switching in the same direction.

Table 12. Typical power dissipation capacitanceVoltages are referenced to GND (ground = 0 V). [\[1\]\[2\]](#)

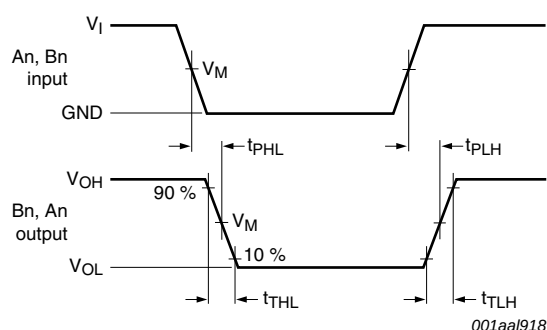
Symbol	Parameter	Conditions	V _{CC(A)}							Unit
			1.2 V	1.2 V	1.5 V	1.8 V	2.5 V	2.5 V	3.3 V	
			V _{CC(B)}							
			1.8 V	5.0 V	1.8 V	1.8 V	2.5 V	5.0 V	3.3 V to 5.0 V	

 $T_{amb} = 25\text{ }^{\circ}\text{C}$

C_{PD}	power dissipation capacitance	outputs enabled; OE = $V_{CC(A)}$								
		A port: (direction A to B)	5	5	5	5	5	5	5	pF
		A port: (direction B to A)	8	8	8	8	8	8	8	pF
		B port: (direction A to B)	18	18	18	18	18	18	18	pF
		B port: (direction B to A)	13	16	12	12	12	12	13	pF
		outputs disabled; OE = GND								
		A port: (direction A to B)	0.12	0.12	0.04	0.05	0.08	0.08	0.07	pF
		A port: (direction B to A)	0.01	0.01	0.01	0.01	0.01	0.01	0.01	pF
		B port: (direction A to B)	0.01	0.01	0.01	0.01	0.01	0.01	0.01	pF
		B port: (direction B to A)	0.07	0.09	0.07	0.07	0.05	0.09	0.09	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW). $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where: f_i = input frequency in MHz; f_o = output frequency in MHz; C_L = load capacitance in pF; V_{CC} = supply voltage in V; N = number of inputs switching; $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.[2] $f_i = 10\text{ MHz}$; $V_i = \text{GND to } V_{CC}$; $t_r = t_f = 1\text{ ns}$; $C_L = 0\text{ pF}$; $R_L = \infty\text{ }\Omega$.

12. Waveforms

Measurement points are given in [Table 13](#). V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.**Fig 5. Data input (An, Bn) to data output (Bn, An) propagation delay times**

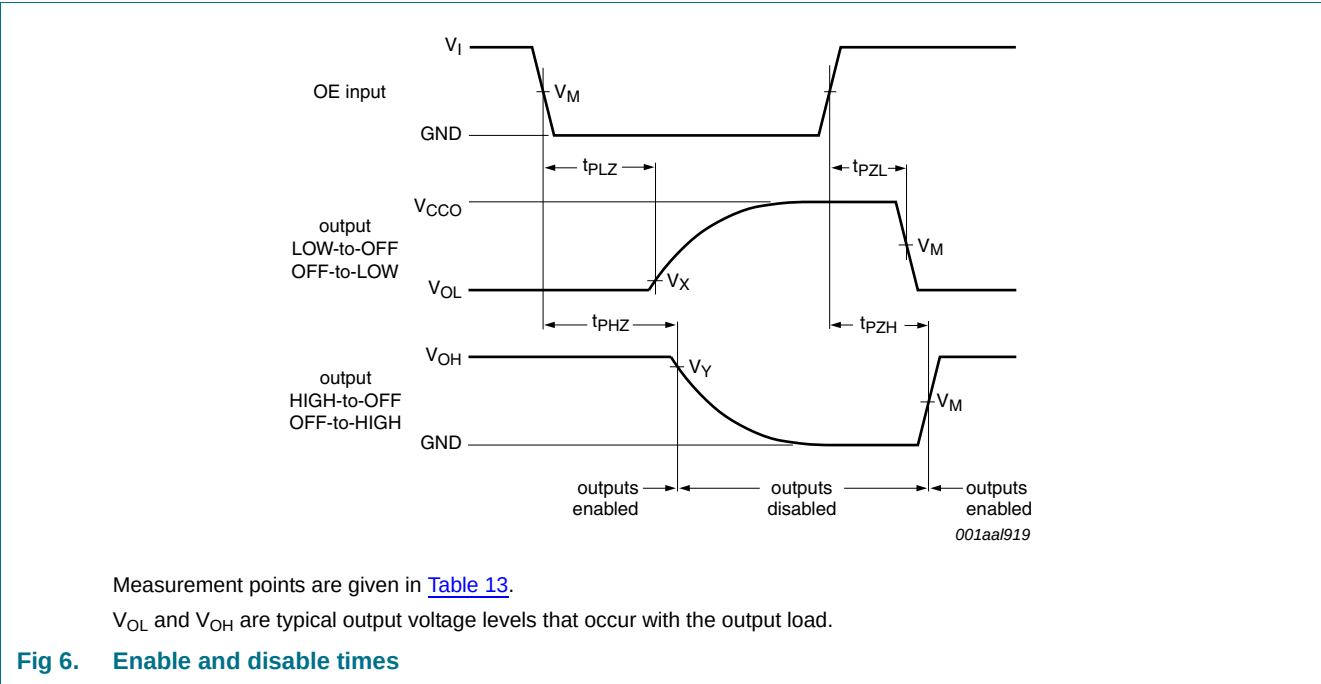


Table 13. Measurement points^[1]

Supply voltage	Input	Output		
V _{CCO}	V _M	V _M	V _X	V _Y
1.2 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.1 V	V _{OH} - 0.1 V
1.5 V ± 0.1 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.1 V	V _{OH} - 0.1 V
1.8 V ± 0.15 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} - 0.15 V
2.5 V ± 0.2 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} - 0.15 V
3.3 V ± 0.3 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	V _{OH} - 0.3 V
5.0 V ± 0.5 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	V _{OH} - 0.3 V

[1] V_{CCI} is the supply voltage associated with the input and V_{CCO} is the supply voltage associated with the output.

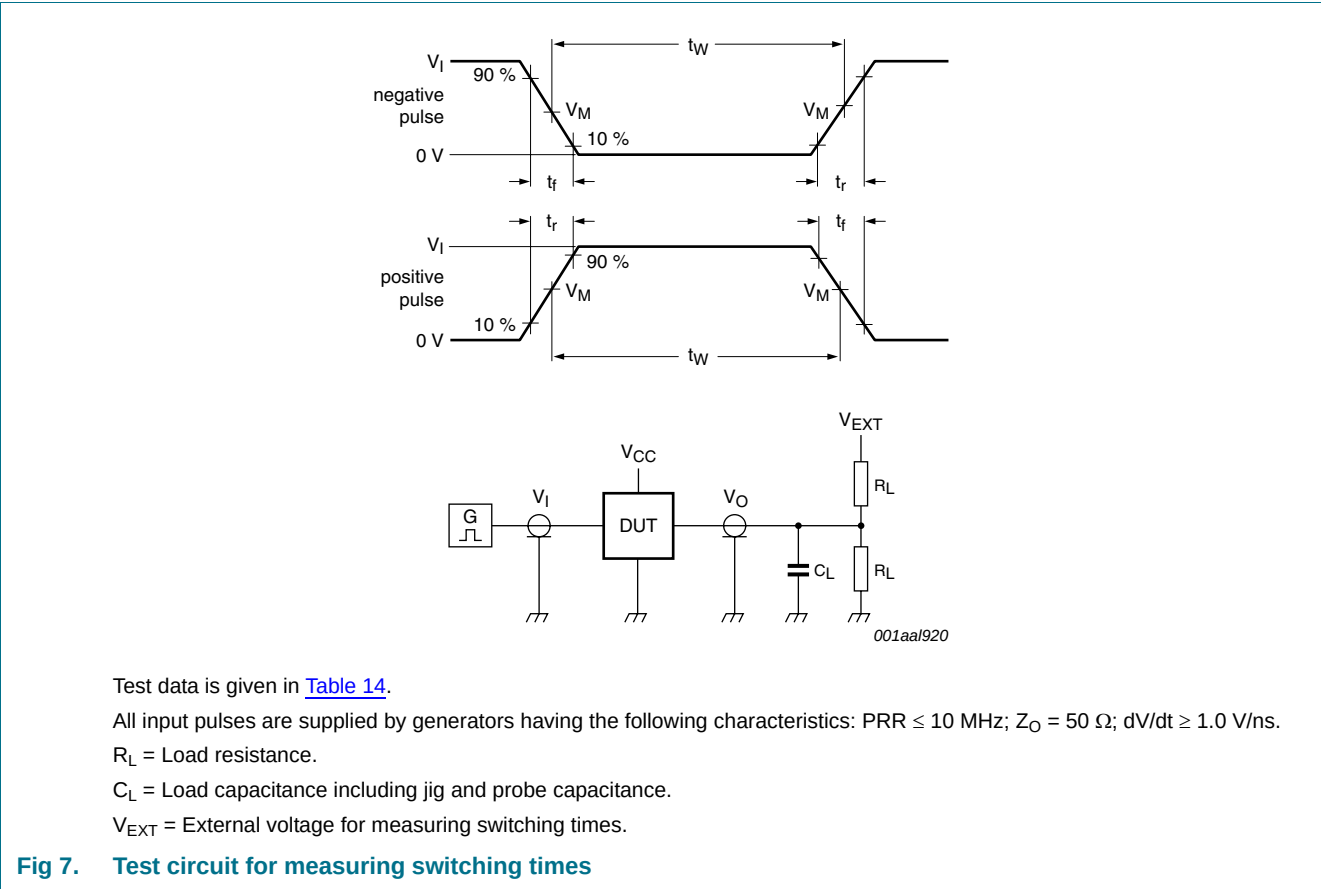


Table 14. Test data

Supply voltage		Input		Load		V _{EXT}		
V _{CC(A)}	V _{CC(B)}	V _I ^[1]	Δt/ΔV	C _L	R _L ^[2]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ} ^[3]
1.2 V to 3.6 V	1.65 V to 5.5 V	V _{CCI}	≤ 1.0 ns/V	15 pF	50 kΩ, 1 MΩ	open	open	2V _{CCO}

- [1] V_{CCI} is the supply voltage associated with the input.
- [2] For measuring data rate, pulse width, propagation delay and output rise and fall measurements, R_L = 1 MΩ; for measuring enable and disable times, R_L = 50 kΩ.
- [3] V_{CCO} is the supply voltage associated with the output.

13. Application information

13.1 Applications

Voltage level-translation applications. The NXB0102 can be used to interface between devices or systems operating at different supply voltages. See [Figure 8](#) for a typical operating circuit using the NXB0102.

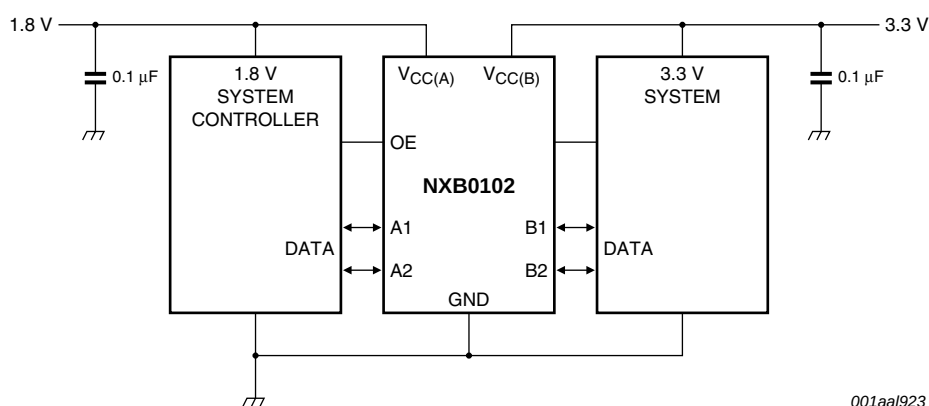


Fig 8. Typical operating circuit

13.2 Architecture

The architecture of the NXB0102 is shown in [Figure 9](#). The device does not require an extra input signal to control the direction of data flow from A to B or from B to A. In a static state, the output drivers of the NXB0102 can maintain a defined output level, but the output architecture is designed to be weak, so that they can be overdriven by an external driver when data on the bus starts flowing in the opposite direction. The output of one-shot circuits detect rising or falling edges on the A or B ports. During a rising edge, the one-shot circuits turn on the PMOS transistors (T1, T3) for a short duration, accelerating the LOW-to-HIGH transition. Similarly, during a falling edge, the one-shot circuits turn on the NMOS transistors (T2, T4) for a short duration, accelerating the HIGH-to-LOW transition. During output transitions the typical output impedance is 70 Ω at $V_{CCO} = 1.2$ V to 1.8 V, 50 Ω at $V_{CCO} = 1.8$ V to 3.3 V and 40 Ω at $V_{CCO} = 3.3$ V to 5.0 V.

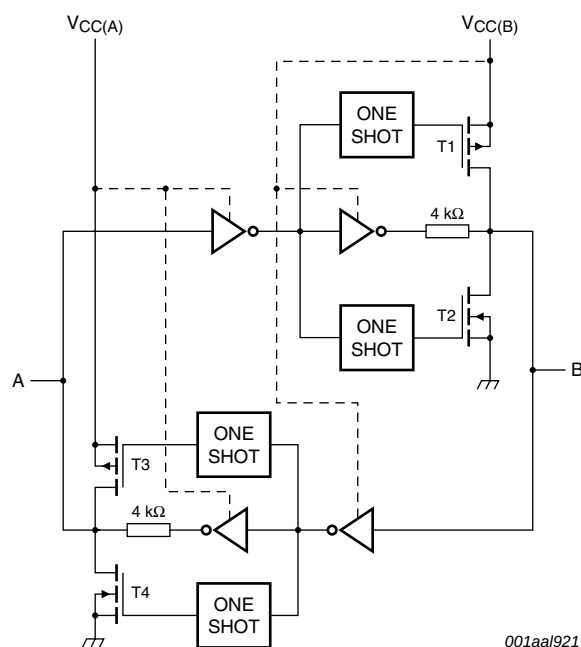
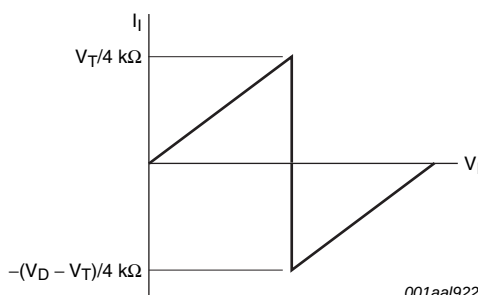


Fig 9. Architecture of NXB0102 I/O cell (one channel)

13.3 Input driver requirements

For correct operation, the device driving the data I/Os of the NXB0102 must have a minimum drive capability of ± 2 mA. See [Figure 10](#) for a plot of typical input current versus input voltage.



V_T : input threshold voltage of the NXB0102 (typically $V_{CCI} / 2$).

V_D : supply voltage of the external driver.

Fig 10. Typical input current versus input voltage graph

13.4 Power-up

During operation $V_{CC(A)}$ must never be higher than $V_{CC(B)}$, however during power-up $V_{CC(A)} \geq V_{CC(B)}$ does not damage the device, so either power supply can be ramped up first. There is no special power-up sequencing required. The NXB0102 includes circuitry that disables all output ports when either $V_{CC(A)}$ or $V_{CC(B)}$ is switched off.

13.5 Enable and disable

An output enable input (OE) is used to disable the device. Setting OE = LOW causes all I/Os to assume the high-impedance OFF-state. The disable time (t_{dis} with no external load) indicates the delay between when OE goes LOW and when outputs actually become disabled. The enable time (t_{en}) indicates the amount of time the user must allow for one one-shot circuitry to become operational after OE is taken HIGH. To ensure the high-impedance OFF-state during power-up or power-down, pin OE should be tied to GND through a pull-down resistor, the minimum value of the resistor is determined by the current-sourcing capability of the driver.

13.6 Pull-up or pull-down resistors on I/O lines

As mentioned previously the NXB0102 is designed with low static drive strength to drive capacitive loads of up to 70 pF. To avoid output contention issues, any pull-up or pull-down resistors used must be above 50 kΩ. For this reason the NXB0102 is not recommended for use in open drain driver applications such as 1-Wire or I²C-bus. For these applications, the NXS0102 level translator is recommended.

14. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

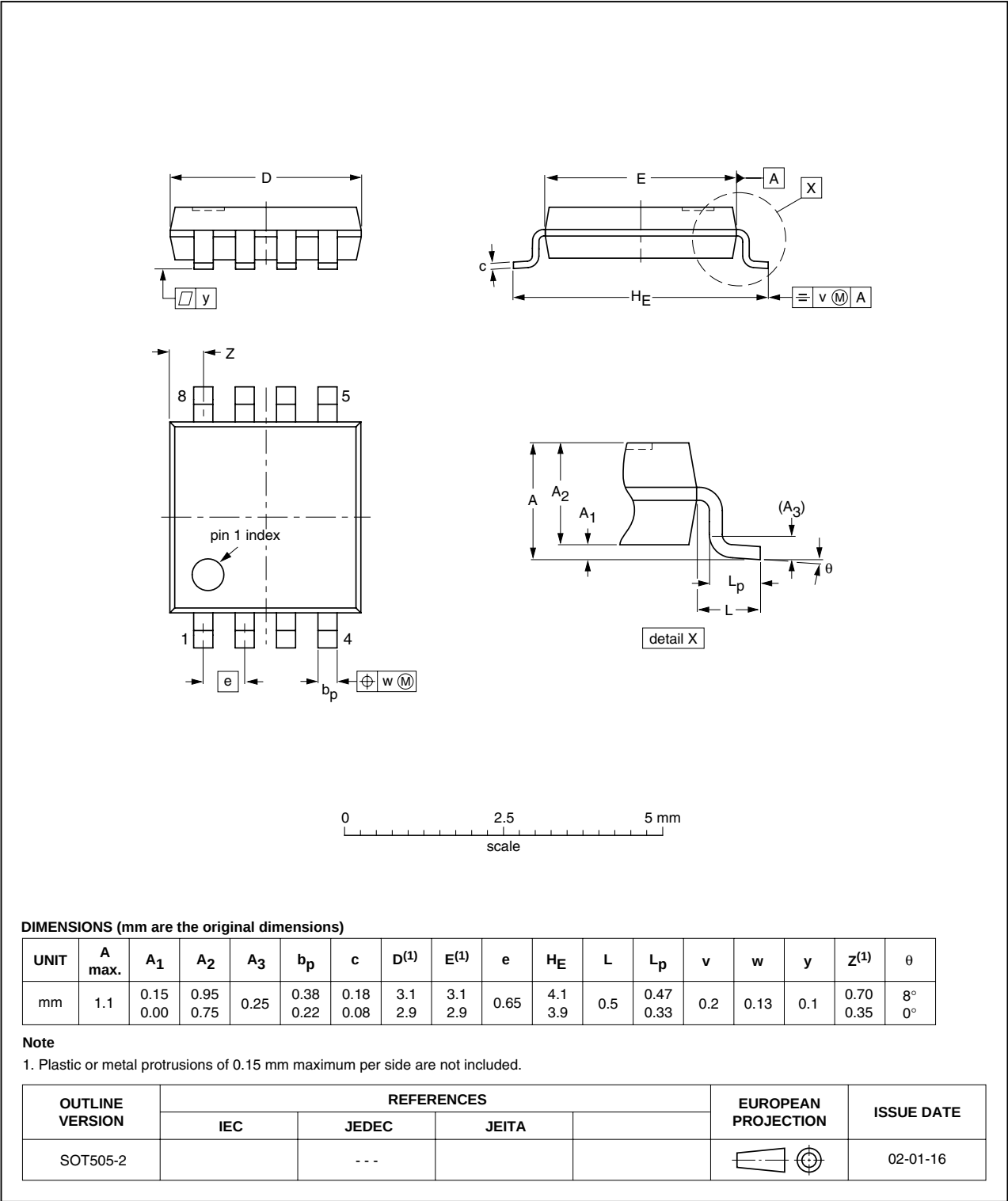


Fig 11. Package outline SOT505-2 (TSSOP8)

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm

SOT833-1

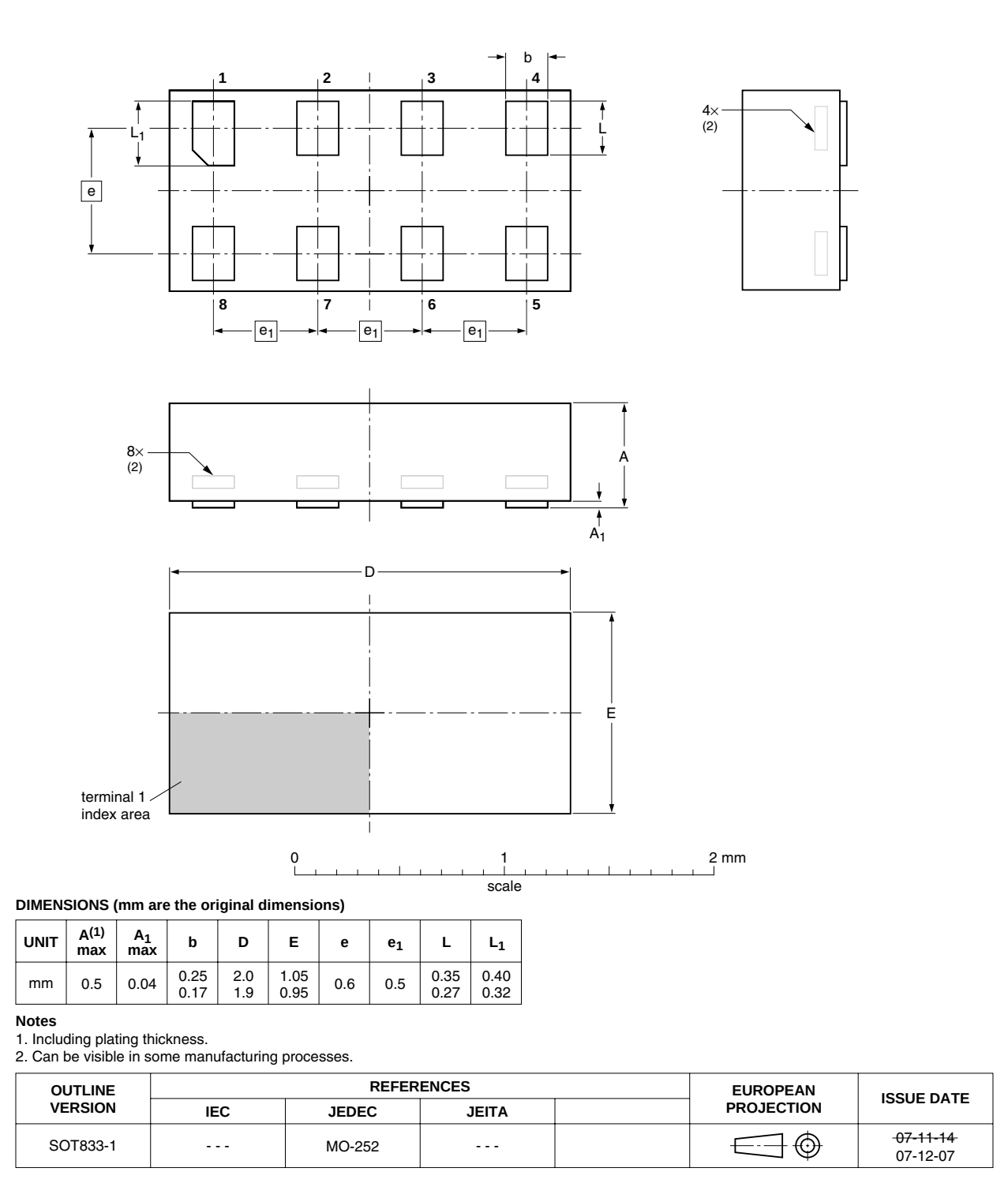


Fig 12. Package outline SOT833-1 (XSON8)

XSON8U: plastic extremely thin small outline package; no leads;
8 terminals; UTLP based; body 3 x 2 x 0.5 mm

SOT996-2

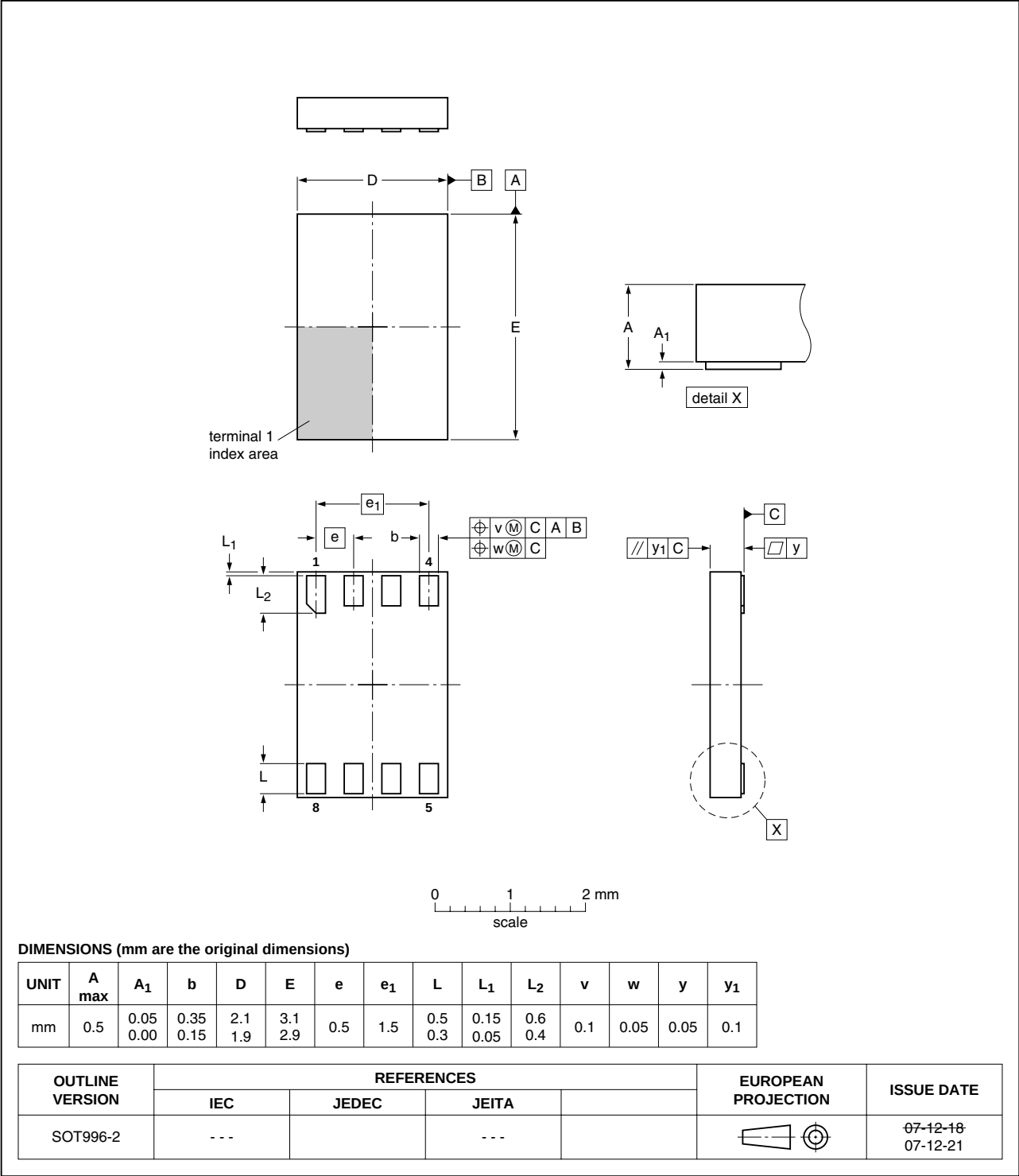


Fig 13. Package outline SOT996-2 (XSON8U)

XSON8: extremely thin small outline package; no leads;
8 terminals; body 1.35 x 1 x 0.5 mm

SOT1089

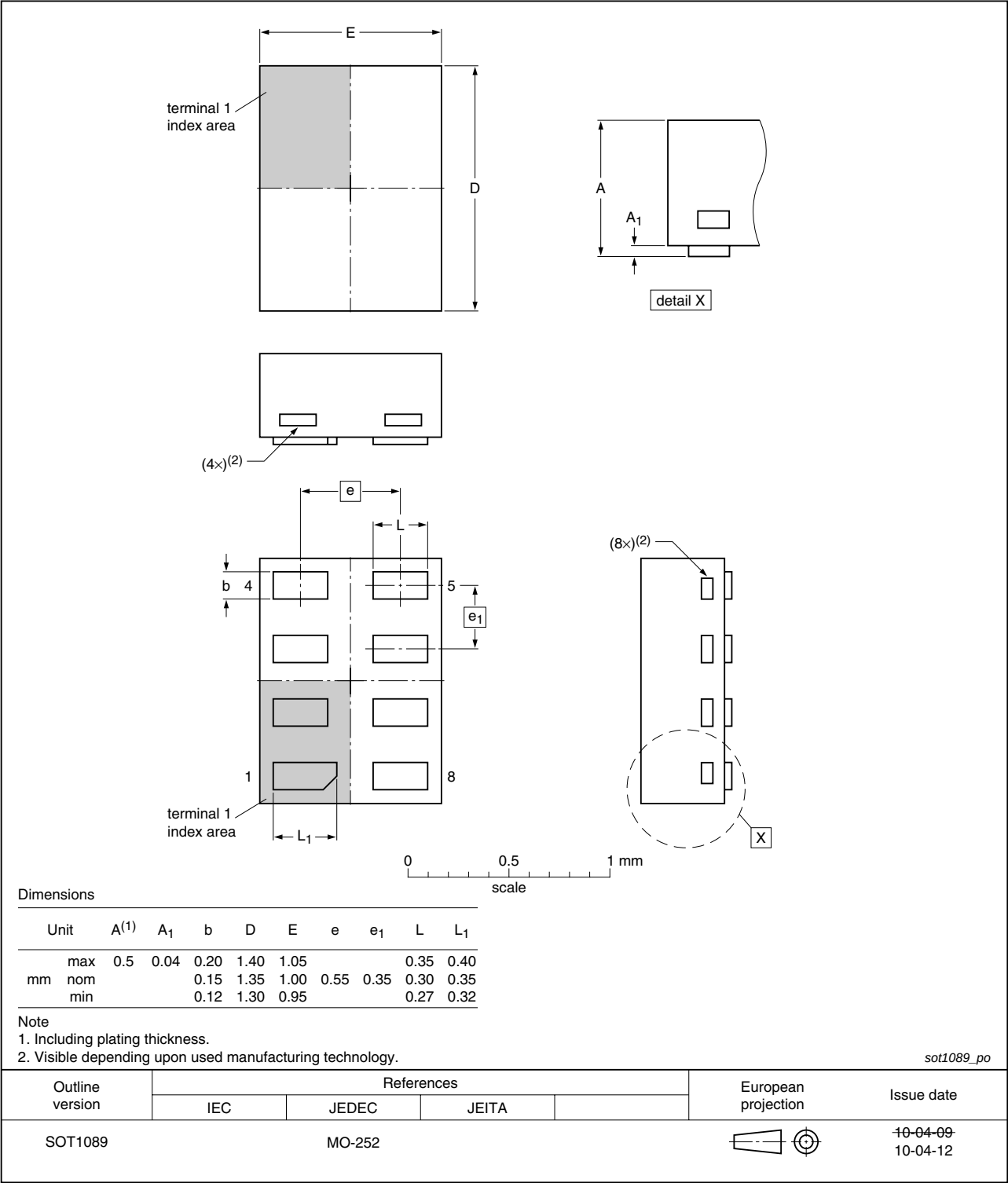


Fig 14. Package outline SOT1089 (XSON8)

15. Abbreviations

Table 15. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
PRR	Pulse Repetition Rate

16. Revision history

Table 16. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NXB0102 v.1	20100608	Product data sheet	-	-

17. Legal information

17.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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